

TDS:EMIC

拓 電 半 導 體

自主封測 品質把控 售後保障

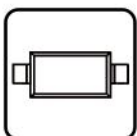
WEB | WWW.TDSEMIC.COM



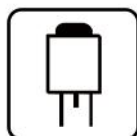
電源管理



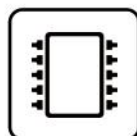
顯示驅動



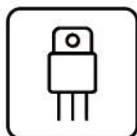
二三極管



LDO穩壓器



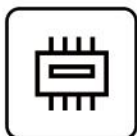
觸摸芯片



MOS管



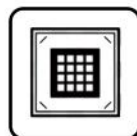
運算放大器



存儲芯片



MCU



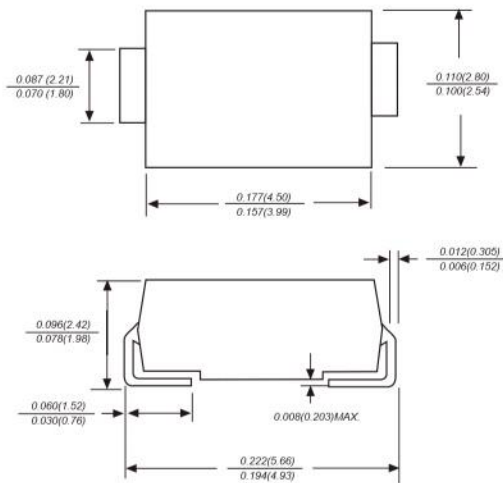
串口通信

ES2D-TD

產品規格說明書

SMA

DO-214AC



Dimensions in inches and (millimeters)

FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Super fast switching for high efficiency
- Low reverse leakage
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

MECHANICAL DATA

Case: JEDEC DO-214AC molded plastic body
Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.003 ounce, 0.093 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	ES2A	ES2B	ES2C	ES2D	ES2E	ES2G	ES2J	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	600	VOLTS
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	420	VOLTS
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	600	VOLTS
Maximum average forward rectified current at T _L =55°C	I _(AV)	2.0							Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	40.0							Amps
Maximum instantaneous forward voltage at 2.0A	V _F	0.95				1.25		1.7	Volts
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	5.0 50.0							mA
Maximum reverse recovery time (NOTE 1)	t _{rr}	35							ns
Typical junction capacitance (NOTE 2)	C _J	60.0							pF
Typical thermal resistance (NOTE 3)	R _{qJA}	40.0							°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +150							°C

Note: 1. Reverse recovery condition $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{rr}=0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

